EEPROM Serial 8-Kb Microwire - Automotive Grade 1

Description

The CAV93C76 is an EEPROM Serial 8-Kb Microwire Automotive Grade 1 device, which is configured as either registers of 16 bits (ORG pin at V_{CC} or Not Connected) or 8 bits (ORG pin at GND). Each register can be written (or read) serially by using the DI (or DO) pin. The CAV93C76 is manufactured using ON Semiconductor's advanced CMOS EEPROM floating gate technology. The device is designed to endure 1,000,000 program/erase cycles and has a data retention of 100 years. The device is available in 8-pin SOIC and TSSOP packages.

Features

- Automotive AEC-Q100 Grade 1 (-40°C to +125°C) Qualified
- High Speed Operation: 2 MHz
- 2.5 V to 5.5 V Supply Voltage Range
- Selectable x8 or x16 Memory Organization
- Self-timed Write Cycle with Auto-clear
- Software Write Protection
- Power-up Inadvertant Write Protection
- Low Power CMOS Technology
- 1,000,000 Program/Erase Cycles
- 100 Year Data Retention
- Sequential Read
- 8-pin SOIC and TSSOP Packages
- This Device is Pb–Free, Halogen Free/BFR Free and RoHS Compliant[†]

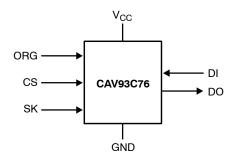


Figure 1. Functional Symbol



ON Semiconductor®

www.onsemi.com



PIN CONFIGURATION



SOIC (V), TSSOP (Y) (Top View)

PIN FUNCTION

Pin Name	Function			
CS	Chip Select			
SK	Serial Clock Input			
DI	Serial Data Input			
DO	Serial Data Output			
V _{CC}	Power Supply			
GND	Ground			
ORG	Memory Organization			
NC	No Connection			

NOTE: When the ORG pin is connected to V_{CC} , the x16 organization is selected. When it is connected to ground, the x8 organization is selected. If the ORG pin is left unconnected, then an internal pull–up device will select the x16 organization.

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 8 of this data sheet.

[†]For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

Table 1. ABSOLUTE MAXIMUM RATINGS

Parameters	Ratings	Units
Storage Temperature	–65 to +150	°C
Voltage on any Pin with Respect to Ground (Note 1)	–0.5 to +6.5	V

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. The minimum DC input voltage is -0.5 V. During transitions, inputs may undershoot to -2.0 V for periods of less than 20 ns. Maximum DC voltage on output pins is V_{CC} +0.5 V, which may overshoot to V_{CC} +2.0 V for periods of less than 20 ns.

Table 2. RELIABILITY CHARACTERISTICS (Note 2)

Symbol	Parameter	Min	Units
N _{END} (Note 3)	Endurance	1,000,000	Program / Erase Cycles
T _{DR}	Data Retention	100	Years

2. These parameters are tested initially and after a design or process change that affects the parameter according to appropriate AEC–Q100 and JEDEC test methods.

3. Block Mode, $V_{CC} = 5 V$, $25^{\circ}C$

Table 3. D.C. OPERATING CHARACTERISTICS

(V_{CC} = +2.5 V to +5.5 V, T_A = -40°C to +125°C, unless otherwise specified.)

Symbol	Parameter	Test Conditions	Min	Max	Units
I _{CC1}	Supply Current (Write)	Write, V _{CC} = 5.0 V		2	mA
I _{CC2}	Supply Current (Read)	Read, DO open, f_{SK} = 2 MHz, V_{CC} = 5.0 V		500	μA
I _{SB1}	Standby Current (x8 Mode)	V _{IN} = GND or V _{CC} CS = GND, ORG = GND		5	μΑ
I _{SB2}	Standby Current (x16 Mode)	$V_{IN} = GND \text{ or } V_{CC}$ CS = GND, ORG = Float or V_{CC}		3	μΑ
Ι _{LI}	Input Leakage Current	$V_{IN} = GND$ to V_{CC}		2	μA
I _{LO}	Output Leakage Current	V _{OUT} = GND to V _{CC} CS = GND		2	μΑ
V _{IL1}	Input Low Voltage	$4.5 \text{ V} \le \text{V}_{\text{CC}} < 5.5 \text{ V}$	-0.1	0.8	V
V _{IH1}	Input High Voltage	$4.5 \text{ V} \le \text{V}_{CC} < 5.5 \text{ V}$	2	V _{CC} + 1	V
V _{IL2}	Input Low Voltage	$2.5 \text{ V} \le \text{V}_{\text{CC}} < 4.5 \text{ V}$	0	V _{CC} x 0.2	V
V _{IH2}	Input High Voltage	$2.5 \text{ V} \le \text{V}_{\text{CC}} < 4.5 \text{ V}$	V _{CC} x 0.7	V _{CC} + 1	V
V _{OL1}	Output Low Voltage	4.5 V \leq V _{CC} < 5.5 V, I _{OL} = 3 mA		0.4	V
V _{OH1}	Output High Voltage	4.5 V \leq V_{CC} < 5.5 V, I_{OH} = -400 μA	2.4		V
V _{OL2}	Output Low Voltage	$2.5 \text{ V} \leq \text{V}_{CC}$ < 4.5 V , I_{OL} = 1 mA		0.2	V
V _{OH2}	Output High Voltage	2.5 V \leq V_{CC} < 4.5 V, I_{OH} = –100 μA	V _{CC} – 0.2		V

Table 4. PIN CAPACITANCE (Note 4)

Symbol	Test	Conditions	Min	Тур	Max	Units
C _{OUT}	Output Capacitance (DO)	V _{OUT} = 0 V			5	pF
C _{IN}	Input Capacitance (CS, SK, DI, ORG)	V _{IN} = 0 V			5	pF

4. These parameters are tested initially and after a design or process change that affects the parameter.

Table 5. POWER-UP TIMING (Notes 6, 5)

Symbol	Parameter	Max	Units
t _{PUR}	Power-up to Read Operation	1	ms
t _{PUW}	Power-up to Write Operation		ms

5. t_{PUR} and t_{PUW} are the delays required from the time V_{CC} is stable until the specified operation can be initiated.

Table 6. A.C. TEST CONDITIONS

Input Rise and Fall Times	≤ 50 ns		
Input Pulse Voltages	0.4 V to 2.4 V	$4.5~\textrm{V} \leq \textrm{V}_{\textrm{CC}} \leq 5.5~\textrm{V}$	
Timing Reference Voltages	0.8 V, 2.0 V	$4.5~\textrm{V} \leq \textrm{V}_{\textrm{CC}} \leq 5.5~\textrm{V}$	
Input Pulse Voltages	0.2 V_{CC} to 0.7 V_{CC}	$2.5~V \leq V_{CC} \leq 4.5~V$	
Timing Reference Voltages	0.5 V _{CC}	$2.5~\textrm{V} \leq \textrm{V}_{\textrm{CC}} \leq 4.5~\textrm{V}$	
Output Load	Current Source I _{OLmax} /I _{OHmax} ; CL = 100 pF		

Table 7. A.C. CHARACTERISTICS (V_{CC} = +2.5 V to +5.5 V, T_A = -40^{\circ}C to +125°C, unless otherwise specified.)

Symbol	Parameter	Min	Max	Units
t _{CSS}	CS Setup Time	50		ns
t _{CSH}	CS Hold Time	0		ns
t _{DIS}	DI Setup Time	100		ns
t _{DIH}	DI Hold Time	100		ns
t _{PD1}	Output Delay to 1		0.25	μs
t _{PD0}	Output Delay to 0		0.25	μs
t _{HZ} (Note 6)	Output Delay to High–Z		100	ns
t _{EW}	Program/Erase Pulse Width		5	ms
t _{CSMIN}	Minimum CS Low Time	0.25		μs
t _{SKHI}	Minimum SK High Time	0.25		μs
t _{SKLOW}	Minimum SK Low Time	0.25		μs
t _{SV}	Output Delay to Status Valid		0.25	μs
SK _{MAX}	Maximum Clock Frequency	DC	2000	kHz

6. This parameter is tested initially and after a design or process change that affects the parameter.

Table 8. INSTRUCTION SET (Note 7)

	Start		Address		D	ata	
Instruction	Bit	Opcode	x8	x16	x8	x16	Comments
READ	1	10	A10–A0	A9-A0			Read Address AN- A0
ERASE	1	11	A10–A0	A9-A0			Clear Address AN- A0
WRITE	1	01	A10–A0	A9-A0	D7-D0	D15-D0	Write Address AN– A0
EWEN	1	00	11XXXXXXXXX	11XXXXXXXX			Write Enable
EWDS	1	00	00XXXXXXXXX	00XXXXXXXX			Write Disable
ERAL	1	00	10XXXXXXXXX	10XXXXXXXX			Clear All Addresses
WRAL	1	00	01XXXXXXXXX	01XXXXXXXX	D7-D0	D15-D0	Write All Addresses

7. Address bit A10 for the 1,024x8 org. and A9 for the 512x16 org. are "don't care" bits, but must be kept at either a "1" or "0" for READ, WRITE and ERASE commands.

Device Operation

The CAV93C76 is a 8192-bit nonvolatile memory intended for use with industry standard microprocessors. The CAV93C76 can be organized as either registers of 16 bits or 8 bits. When organized as X16, seven 13-bit instructions control the read, write and erase operations of the device. When organized as X8, seven 14-bit instructions control the read, write and erase operations of the device. The CAV93C76 operates on a single power supply and will generate on chip, the high voltage required during any write operation.

Instructions, addresses, and write data are clocked into the DI pin on the rising edge of the clock (SK). The DO pin is normally in a high impedance state except when reading data from the device, or when checking the ready/busy status after a write operation.

The ready/busy status can be determined after the start of a write operation by selecting the device (CS high) and polling the DO pin; DO low indicates that the write operation is not completed, while DO high indicates that the device is ready for the next instruction. If necessary, the DO pin may be placed back into a high impedance state during chip select by shifting a dummy "1" into the DI pin. The DO pin will enter the high impedance state on the falling edge of the clock (SK). Placing the DO pin into the high impedance state is recommended in applications where the DI pin and the DO pin are to be tied together to form a common DI/O pin.

The format for all instructions sent to the device is a logical "1" start bit, a 2-bit (or 4-bit) opcode, 10-bit address (an additional bit when organized X8) and for write operations a 16-bit data field (8-bit for X8 organizations). The most significant bit of the address is "don't care" but it must be present.

Read

Upon receiving a READ command and an address (clocked into the DI pin), the DO pin of the CAV93C76 will come out of the high impedance state and, after sending an initial dummy zero bit, will begin shifting out the data addressed (MSB first). The output data bits will toggle on the rising edge of the SK clock and are stable after the specified time delay (t_{PD0} or t_{PD1}).

For the CAV93C76, after the initial data word has been shifted out and CS remains asserted with the SK clock continuing to toggle, the device will automatically increment to the next address and shift out the next data word in a sequential READ mode. As long as CS is continuously asserted and SK continues to toggle, the device will keep incrementing to the next address automatically until it reaches the end of the address space, then loops back to address 0. In the sequential READ mode, only the initial data word is preceeded by a dummy zero bit. All subsequent data words will follow without a dummy zero bit.

Write

After receiving a WRITE command, address and the data, the CS (Chip Select) pin must be deselected for a minimum of t_{CSMIN} . The falling edge of CS will start the self clocking clear and data store cycle of the memory location specified in the instruction. The clocking of the SK pin is not necessary after the device has entered the self clocking mode. The ready/busy status of the CAV93C76 can be determined by selecting the device and polling the DO pin. Since this device features Auto–Clear before write, it is NOT necessary to erase a memory location before it is written into.

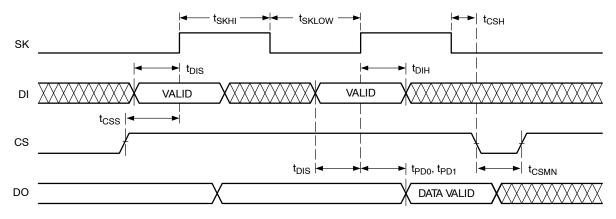


Figure 2. Synchronous Data Timing

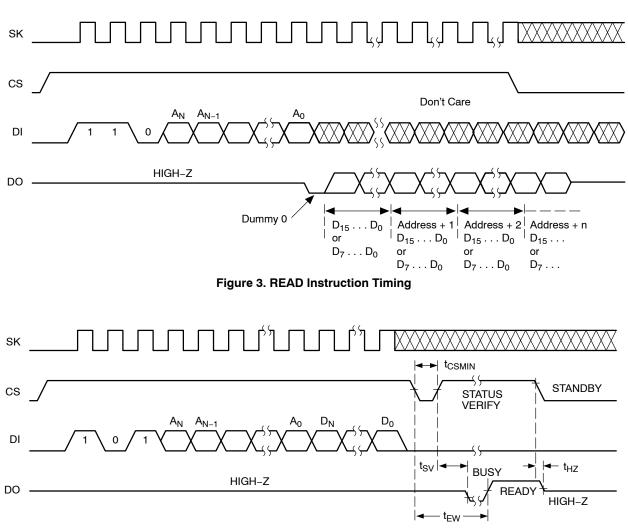


Figure 4. WRITE Instruction Timing

Erase

Upon receiving an ERASE command and address, the CS (Chip Select) pin must be deasserted for a minimum of t_{CSMIN} . The falling edge of CS will start the self clocking clear cycle of the selected memory location. The clocking of the SK pin is not necessary after the device has entered the self clocking mode. The ready/busy status of the CAV93C76 can be determined by selecting the device and polling the DO pin. Once cleared, the content of a cleared location returns to a logical "1" state.

Erase/Write Enable and Disable

The CAV93C76 powers up in the write disable state. Any writing after power-up or after an EWDS (write disable) instruction must first be preceded by the EWEN (write enable) instruction. Once the write instruction is enabled, it will remain enabled until power to the device is removed, or the EWDS instruction is sent. The EWDS instruction can be used to disable all CAV93C76 write and clear instructions, and will prevent any accidental writing or clearing of the device. Data can be read normally from the device regardless of the write enable/disable status.

Erase All

Upon receiving an ERAL command, the CS (Chip Select) pin must be deselected for a minimum of t_{CSMIN} . The falling edge of CS will start the self clocking clear cycle of all memory locations in the device. The clocking of the SK pin is not necessary after the device has entered the self clocking mode. The ready/busy status of the CAV93C76 can be

determined by selecting the device and polling the DO pin. Once cleared, the contents of all memory bits return to a logical "1" state.

Write All

Upon receiving a WRAL command and data, the CS (Chip Select) pin must be deselected for a minimum of t_{CSMIN} . The falling edge of CS will start the self clocking data write to all memory locations in the device. The clocking of the SK pin is not necessary after the device has entered the self clocking mode. The ready/busy status of the CAV93C76 can be determined by selecting the device and polling the DO pin. It is not necessary for all memory locations to be cleared before the WRAL command is executed.

Note 1: After the last data bit has been sampled, Chip Select (CS) must be brought Low before the next rising edge of the clock (SK) in order to start the self-timed high voltage cycle. This is important because if CS is brought low before or after this specific frame window, the addressed location will not be programmed or erased.

Power-On Reset (POR)

The CAV93C76 incorporates Power–On Reset (POR) circuitry which protects the device against malfunctioning while V_{CC} is lower than the recommended operating voltage.

The device will power up into a read–only state and will power–down into a reset state when V_{CC} crosses the POR level of ~1.3 V.

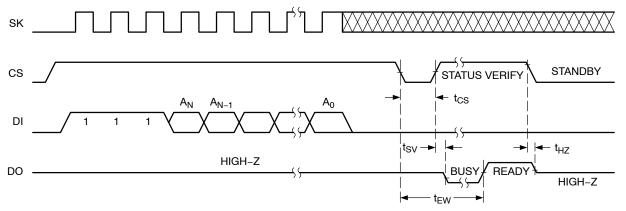
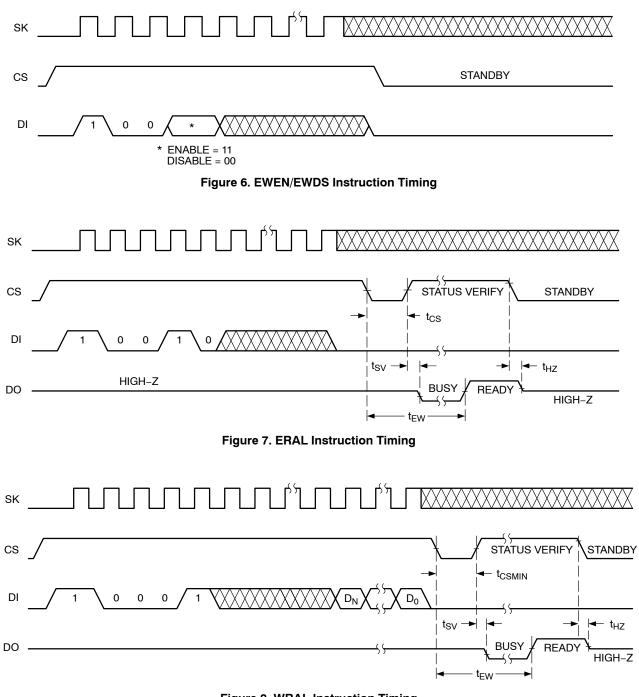


Figure 5. ERASE Instruction Timing





ORDERING INFORMATION

Device Order Number	Specific Device Marking	Package Type	Temperature Range	Lead Finish	Shipping [†]
CAV93C76VE-GT3	93C76D	SOIC-8, JEDEC	–40°C to +125°C	NiPdAu	Tape & Reel, 3,000 Units / Reel
CAV93C76YE-GT3	M76D	TSSOP-8	–40°C to +125°C	NiPdAu	Tape & Reel, 3,000 Units / Reel

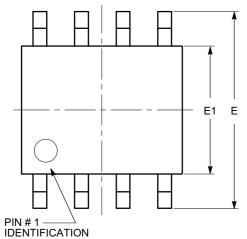
+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
All packages are RoHS-compliant (Lead-free, Halogen-free).
The standard lead finish is NiPdAu.

 For additional package and temperature options, please contact your nearest ON Semiconductor sales office.
For detailed information and a breakdown of device nomenclature and numbering systems, please see the ON Semiconductor Device Nomenclature document, TND310/D, available at www.onsemi.com



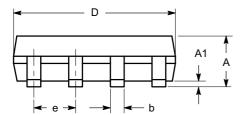
SOIC 8, 150 mils CASE 751BD-01 ISSUE O

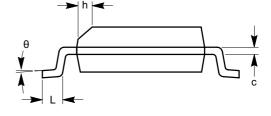
DATE 19 DEC 2008



TOP VIEW

SYMBOL	MIN	NOM	MAX
А	1.35		1.75
A1	0.10		0.25
b	0.33		0.51
с	0.19		0.25
D	4.80		5.00
E	5.80		6.20
E1	3.80		4.00
е		1.27 BSC	
h	0.25		0.50
L	0.40		1.27
θ	0°		8°





END VIEW

SIDE VIEW

Notes:

(1) All dimensions are in millimeters. Angles in degrees.(2) Complies with JEDEC MS-012.

DOCUMENT NUMBER:	98AON34272E	Electronic versions are uncontrolled exce		
STATUS:	ON SEMICONDUCTOR STANDARD	accessed directly from the Document versions are uncontrolled except		
REFERENCE:		"CONTROLLED COPY" in red.		
DESCRIPTION:	SOIC 8, 150 MILS		PAGE 1 OF 2	



DOCUMENT NUMBER: 98AON34272E

PAGE 2 OF 2

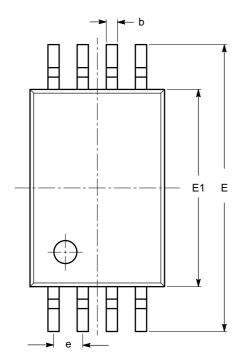
ISSUE	REVISION	DATE
0	RELEASED FOR PRODUCTION FROM POD #SOIC8-002-01 TO ON SEMICONDUCTOR. REQ. BY B. BERGMAN.	19 DEC 2008

ON Semiconductor and are registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.



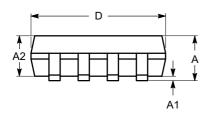
TSSOP8, 4.4x3 CASE 948AL-01 ISSUE O

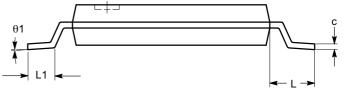
DATE 19 DEC 2008



SYMBOL	MIN	NOM	MAX
А			1.20
A1	0.05		0.15
A2	0.80	0.90	1.05
b	0.19		0.30
с	0.09		0.20
D	2.90	3.00	3.10
Е	6.30	6.40	6.50
E1	4.30	4.40	4.50
е	0.65 BSC		
L	1.00 REF		
L1	0.50	0.60	0.75
θ	0°		8°

TOP VIEW





END VIEW

Notes:

All dimensions are in millimeters. Angles in degrees.
Complies with JEDEC MO-153.

SIDE VIEW

DOCUMENT NUMBER:	98AON34428E	Electronic versions are uncontrollec		
STATUS:	ON SEMICONDUCTOR STANDARD	accessed directly from the Document F versions are uncontrolled except v		
REFERENCE:		"CONTROLLED COPY" in red.		
DESCRIPTION:	TSSOP8, 4.4X3		PAGE 1 OF 2	



DOCUMENT NUMBER: 98AON34428E

PAGE 2 OF 2

ISSUE	REVISION	DATE
0	RELEASED FOR PRODUCTION FROM POD #TSSOP8-004-01 TO ON SEMICONDUCTOR. REQ. BY B. BERGMAN.	19 DEC 2008

ON Semiconductor and are registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other application in which the failure of the SCILLC product culd create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

ON Semiconductor and 💷 are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typical" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that ON Semiconductor was negligent regarding the design or manufacture of the part. ON Semiconductor is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT

Literature Distribution Center for ON Semiconductor 19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada Fax: 303–675–2176 or 800–344–3867 Toll Free USA/Canada Email: orderlit@onsemi.com

N. American Technical Support: 800-282-9855 Toll Free USA/Canada Europe, Middle East and Africa Technical Support:

ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit Phone: 421 33 790 2910

For additional information, please contact your local

Sales Representative